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AIMS AND SCOPE

It is the function of this Journal to bring together in one publication outstanding papers reporting original work in the following areas: (1) applications of solid-state physics in such fields as transistor technology, including theory and design, crystal growth, measurement and evaluation, preparation of junctions and measurement techniques; (2) applications of computer and numerical methods to the modeling of and simulation of solid-state devices; (3) physics and design of ultra-small (submicron) microelectronic devices (VLSI), including methods of processing, measurement and evaluation. Also of interest are applications of intermetallic and binary and ternary semiconductors, the design and performance of power semiconductor devices, solar cells, photoconductors, thermoelectric and ferroelectric devices, galvanomagnetic devices, and electroluminescent devices, including semiconductor lasers. Of particular interest are solid-state optical devices for storage and transfer of information. Papers covering novel topics extending the frontiers of solid-state technology are of course invited. Review papers covering important topics in solid-state electronics will be presented at intervals. Papers will be published in the formats of regular Research Papers, Notes, and Letters to the Editor.

It is expected that, because of its international scope and because it emphasizes the association of theory and practice, the Journal will promote further progress in the ever-widening borderland between solid-state physics and circuit engineering.

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